Elastically Strain-Relaxed GaAs/InGaAs/GaAs Heterostructures on GaAs(001)\textsuperscript{1} D.L. OWEN, D. LACKNER, O.J. PITTS, S.P. WATKINS, P.M. MOONEY, Simon Fraser University — Engineered substrates with surface regions having an in-plane lattice parameter different from that of available semiconductor wafers are of interest to extend the properties of semiconductor devices. This was achieved by bonding strain-relaxed GaAs/In\textsubscript{0.08}Ga\textsubscript{0.92}As/GaAs structures on GaAs(001) substrates. Pseudomorphic heterostructures having a lattice mismatch of 0.56% were grown by metal-organic chemical vapor deposition (MOCVD) and patterned using conventional photolithography to define arrays of 10 or 20 micron square structures. A sacrificial AlAs layer was then removed by selective etching with HF. During etching, the strained structures relax elastically, without introducing misfit dislocations, and bond weakly in-place to the substrate. The degree of strain relaxation of the InGaAs layer is determined by the relative thickness of the GaAs and InGaAs layers in agreement with a force balance model.\textsuperscript{2} The bond was then strengthened by annealing at 400°C for 2hrs, while stabilizing the surface with TBAs in the MOCVD reactor. The increase in the in-plane lattice parameter of the bonded structures compared to the GaAs substrate was 0.25-0.44%.

\textsuperscript{1}National Science and Engineering Research Council


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Date submitted: 10 Apr 2009

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